

BEST WALLBOLK CON

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PATENT ABSTRACTS OF JAPAN

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(74) Representative:

## SEMICONDUCTOR DEVICE (54) MANUFACTURE OF

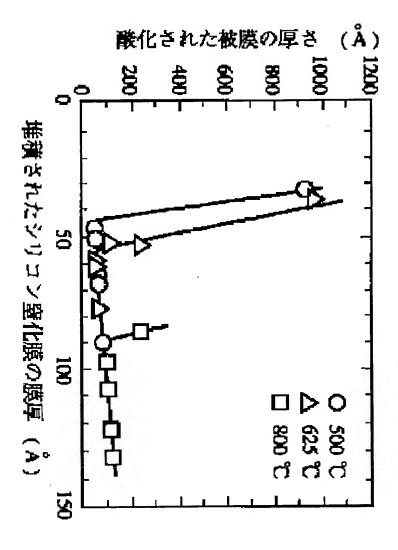
(57) Abstract:

of film formation are compatible with oxidation resistance and high speed wherein the improvement of each other. method of a silicon nitride film PURPOSE: To provide a forming

material gas, at a temperature lower method using silane and ammonia as film is formed by a thermal CVD CONSTITUTION: A silicon nitride

than or equal to 630°C and a pressure higher than or equal to 10Torr. In this case, higher order silane such as disilane and trisilane may be used instead of silane as the material gas, and hydrazine or derivative of hydrazine such as monomethylhydrazine and trimethylhydrazine may be used instead of ammonia as the material gas.

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